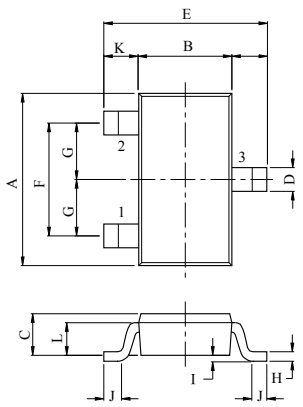
KTA1552T

EPITAXIAL PLANAR PNP TRANSISTOR

DC-DC CONVERTERS RELAY DRIVERS, LAMP DRIVERS,
MOTOR DRIVERS, STROBES APPLICATION.

FEATURES

- Adoption of FBET, MBIT Processes.
- High Current Capacitance.
- Low Collector-to-Emitter Saturation Voltage.
- High-Speed Switching.
- Ultrasmall Package Facilitates Miniaturization in end Products.
- High Allowable Power Dissipation.
- Complementary to KTC3552T.



DIM	MILLIMETERS
A	2 9±0 2
B	1 6+0 2/-0 1
C	0 70±0 05
D	0 4±0 1
E	2 8+0 2/-0 3
F	1 9±0 2
G	0 95
H	0 16±0 05
I	0 00-0 10
J	0 25+0 25/-0 15
K	0 60
L	0 55

1 EMITTER
2 BASE
3 COLLECTOR

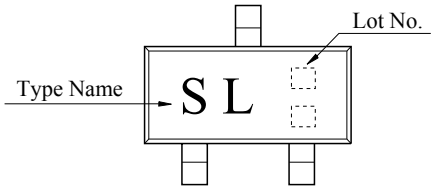
TSM

MAXIMUM RATING (Ta=25℃)

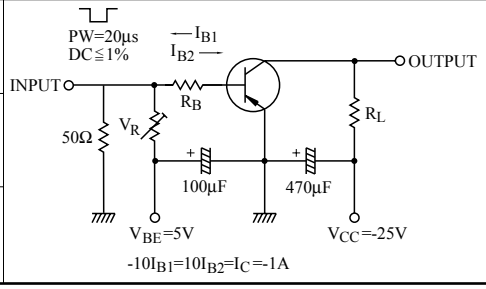
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-50	V
Collector-Emitter Voltage		V_{CES}	-50	V
		V_{CEO}	-50	
Emitter-Base Voltage		V_{EBO}	-6	V
Collector Current	DC	I_C	-3	A
	Pulse	I_{CP}	-6	
Base Current		I_B	-600	mA
Collector Power Dissipation		P_C *	0.9	W
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55～150	℃

* Package mounted on a ceramic board (600㎟×0.8㎜)

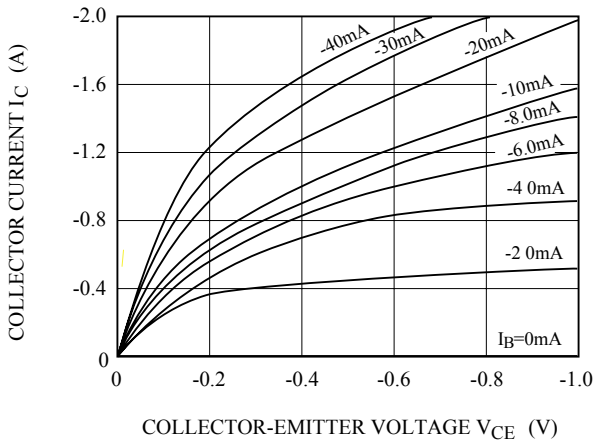
Marking



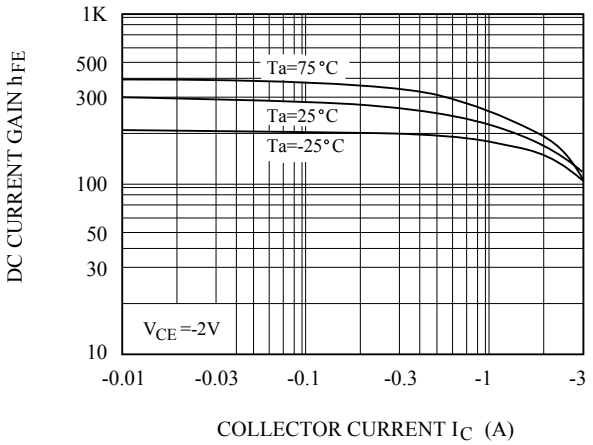
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=-40V, I_E=0	-	-	-0.1	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=-4V, I_C=0	-	-	-0.1	μA
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C=-10μA, I_E=0	-50	-	-	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CES}$	I_C=-100μA, V_{BE}=0	-50	-	-	V
		$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-50	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-6	-	-	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)1}$	I_C=-1A, I_B=-50mA	-	-100	-200	mV
		$V_{CE(sat)2}$	I_C=-2A, I_B=-100mA	-	-185	-500	mV
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C=-2A, I_B=-100mA	-	-0.88	-1.2	V
DC Current Gain		h_{FE}	V_{CE}=-2V, I_C=-100mA	200	-	560	
Transition Frequency		f_T	V_{CE}=-10V, I_C=-500mA	-	360	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=-10V, f=1MHz	-	24	-	pF
Swiitching Time	Turn-On Time	t_{on}		-	30	-	nS
	Storage Time	t_{stg}		-	230	-	
	Fall Time	t_f		-	15	-	

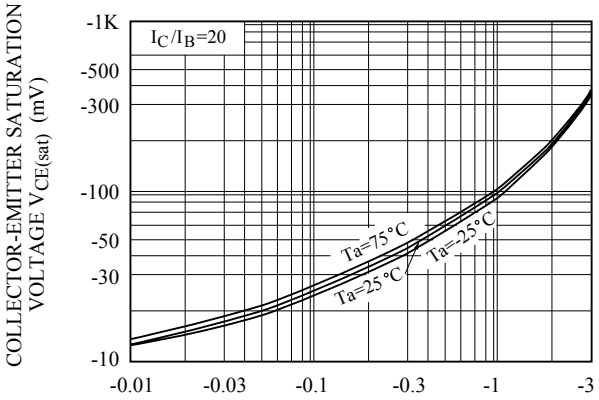
I_C - V_{CE}



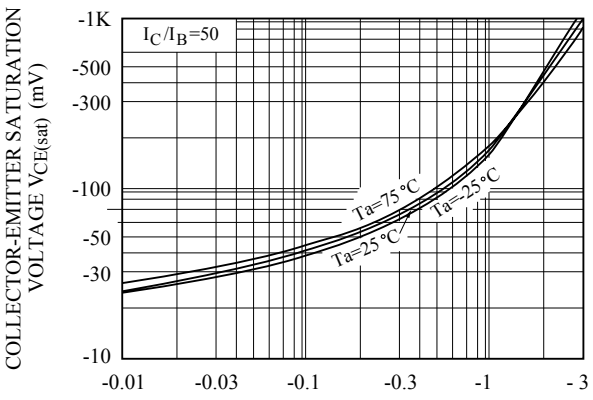
h_{FE} - I_C



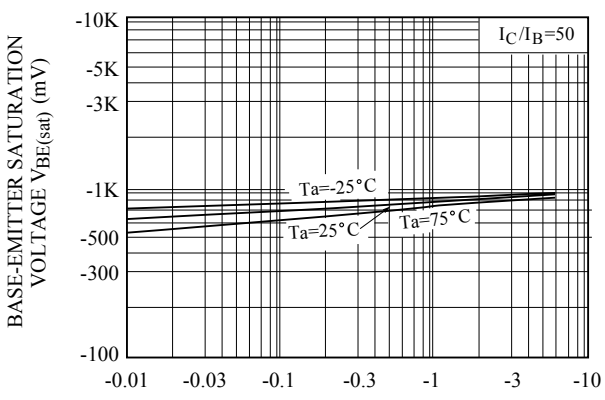
$V_{CE(sat)}$ - I_C



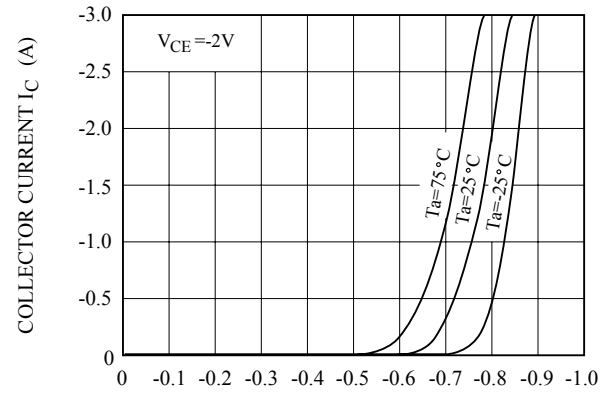
$V_{CE(sat)}$ - I_C



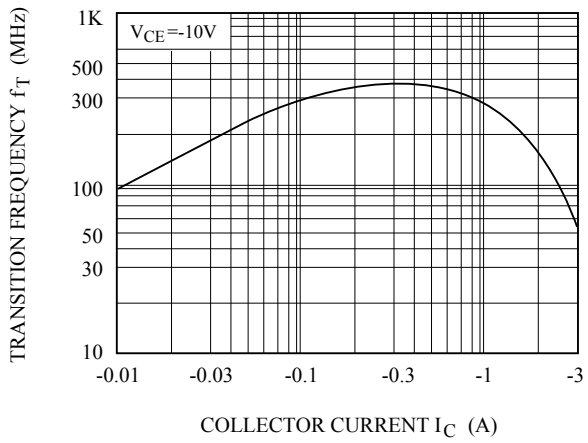
$V_{BE(sat)}$ - I_C



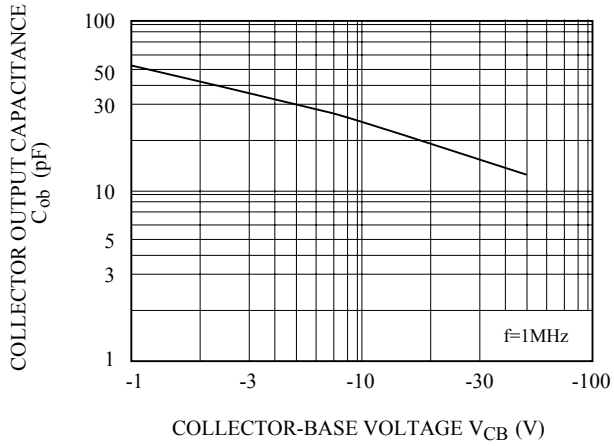
I_C - V_{BE}



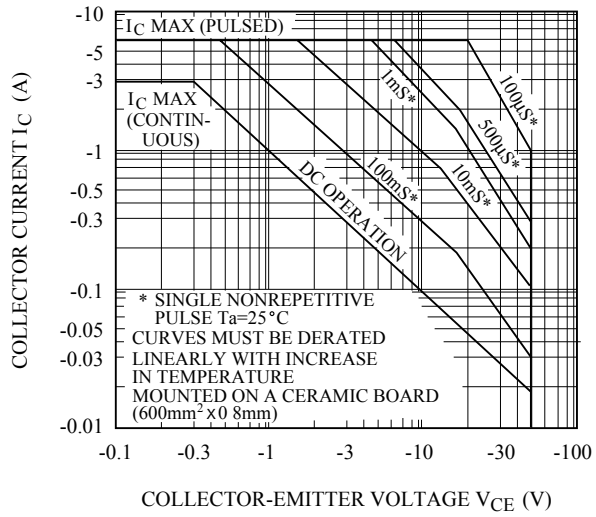
f_T - I_C



C_{ob} - V_{CB}



SAFE OPERATING AREA



Pc - Ta

